

FRED

Ultrafast Soft Recovery Diode, 1200V, 15A

Description:

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery character of the diodes offers buffer in most applications. These devices are suited for power converters and other applications where the switching losses are not significant portion of the total losses.

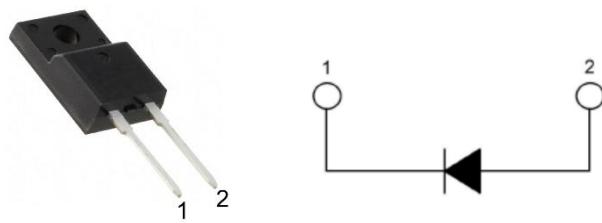
Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low IR value
- Very Low forward voltage
- Epitaxial chip construction

Product Summary	
V_R	1200 V
$I_{F(AV)}$	15 A
t_{rr}	40 ns

Applications:

- Switched mode power supply
- Free wheeling diode, Snubber diode
- UPS



Absolute Maximum Ratings						
Parameter	Symbol	Test Conditions	Values		Units	
Repetitive peak reverse voltage	V_{RRM}			1200	V	
Continuous forward current	$I_{F(AV)}$	$T_A=110^\circ C$		15	A	
Single pulse forward current	I_{FSM}	$T_A=25^\circ C$		120	A	
Maximum repetitive forward current	I_{FRM}	Square wave, 20kHz		30	A	
Operating junction	T_j			175	°C	
Storage temperatures	T_{stg}			-55 to +175	°C	

Electrical characteristics ($T_a=25^\circ C$ unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Breakdown voltage	V_{BR}	$I_R=100\mu A$	1200			V
Blocking voltage	V_R					
Forward voltage	V_F	$I_F=15 A$		2.00	2.60	V
		$I_F=15 A, T_j =125^\circ C$		1.70	2.30	V
Reverse leakage current	I_R	$V_R=V_{RRM}$			20	μA
		$T_j=150^\circ C, V_R=1200V$			200	μA
Reverse recovery time	trr	$I_F=0.5A, I_R=1A, I_{RR}=0.25A$			60	ns
		$I_F=1A, V_R=30V, dI/dt =200A/us$		28	40	ns

Thermal characteristics						
Parameter	Symbol	Typ	MAX		Units	
Junction-to-Case	R_{thJC}	-	4.2		°C/W	

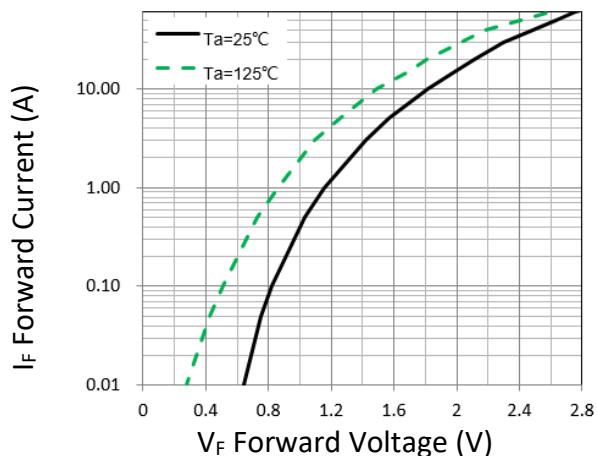


Figure 1. Forward Characteristic(typ.)

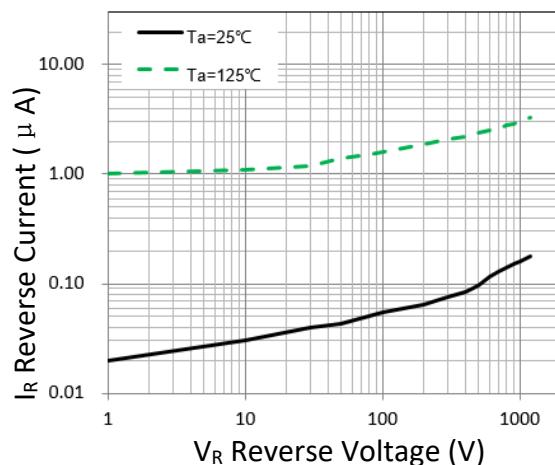


Figure 2. Reverse Characteristic (typ.)

Package Information		
TO-220F-2 PACKAGE		
Symbol	Dimensions(millimeters)	
	Min.	Max.
A	4.35	4.85
A1	2.30	2.70
A2	0.40	0.80
A3	2.10	2.50
b	0.60	1.00
b1	1.00	1.40
c	0.30	0.70
e	4.60	5.40
E	9.90	10.30
E1	6.80	7.20
H	15.6	16.0
H1	8.80	9.20
H2	12.5	13.9
H3	2.90	3.30
G	3.10	3.50
ΦP	3.10	3.50

Detailed description: A technical drawing of the TO-220F-2 package showing its physical dimensions. The drawing includes top and side views with various dimension lines labeled with symbols like A, A1, A2, A3, b, b1, c, e, E, H, H1, H2, H3, G, and ΦP . The top view shows the chip area and lead positions, while the side view provides a detailed look at the lead heights and overall profile.